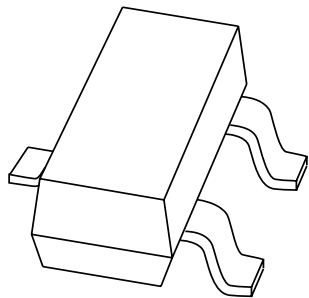


DATA SHEET



BAS19; BAS20; BAS21 General purpose diodes

Product specification
Supersedes data of 1999 May 26

2003 Mar 20

General purpose diodes

BAS19; BAS20; BAS21

FEATURES

- Small plastic SMD package
- Switching speed: max. 50 ns
- General application
- Continuous reverse voltage: max. 100 V; 150 V; 200 V
- Repetitive peak reverse voltage: max. 120 V; 200 V; 250 V
- Repetitive peak forward current: max. 625 mA.

APPLICATIONS

- General purpose switching in e.g. surface mounted circuits.

DESCRIPTION

The BAS19, BAS20 and BAS21 are general purpose diodes fabricated in planar technology, and encapsulated in a small SOT23 plastic SMD package.

MARKING

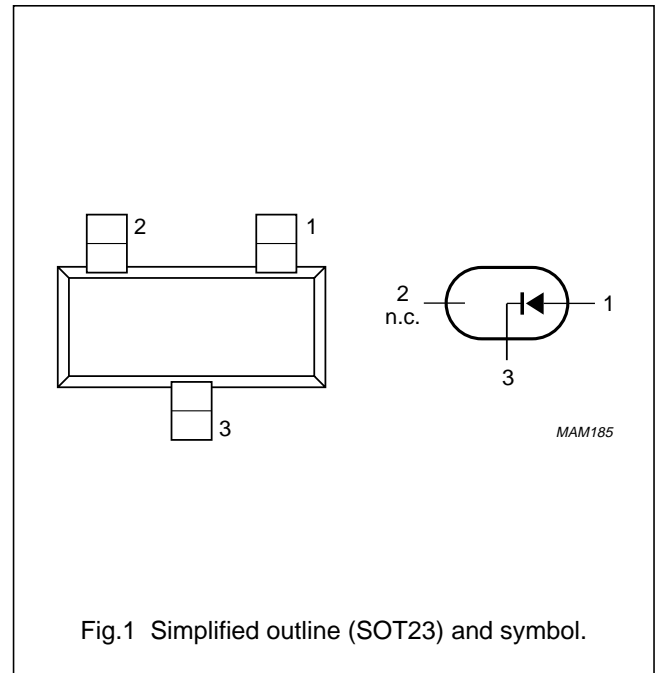
TYPE NUMBER	MARKING CODE ⁽¹⁾
BAS19	JP*
BAS20	JR*
BAS21	JS*

Note

- * = p: Made in Hong Kong.
 * = t: Made in Malaysia.
 * = W: Made in China.

PINNING

PIN	DESCRIPTION
1	anode
2	not connected
3	cathode



General purpose diodes

BAS19; BAS20; BAS21

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BAS19		–	120	V
	BAS20		–	200	V
	BAS21		–	250	V
V_R	continuous reverse voltage				
	BAS19		–	100	V
	BAS20		–	150	V
	BAS21		–	200	V
I_F	continuous forward current	see Fig.2; note 1	–	200	mA
I_{FRM}	repetitive peak forward current		–	625	mA
I_{FSM}	non-repetitive peak forward current	square wave; $T_j = 25\text{ °C}$ prior to surge; see Fig.4			
		$t = 1\ \mu\text{s}$	–	9	A
		$t = 100\ \mu\text{s}$	–	3	A
		$t = 10\ \text{ms}$	–	1.7	A
P_{tot}	total power dissipation	$T_{amb} = 25\text{ °C}$; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Device mounted on an FR4 printed-circuit board.

General purpose diodes

BAS19; BAS20; BAS21

ELECTRICAL CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.3 $I_F = 100\text{ mA}$ $I_F = 200\text{ mA}$	1 1.25	V V
I_R	reverse current BAS19 BAS20 BAS21	see Fig.5 $V_R = 100\text{ V}$ $V_R = 100\text{ V}; T_j = 150\text{ °C}$ $V_R = 150\text{ V}$ $V_R = 150\text{ V}; T_j = 150\text{ °C}$ $V_R = 200\text{ V}$ $V_R = 200\text{ V}; T_j = 150\text{ °C}$	100 100 100 100 100 100	nA μA nA μA nA μA
C_d	diode capacitance	$f = 1\text{ MHz}; V_R = 0$; see Fig.6	5	pF
t_{rr}	reverse recovery time	when switched from $I_F = 30\text{ mA}$ to $I_R = 30\text{ mA}; R_L = 100\ \Omega$; measured at $I_R = 3\text{ mA}$; see Fig.8	50	ns

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-tp}$	thermal resistance from junction to tie-point		330	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	note 1	500	K/W

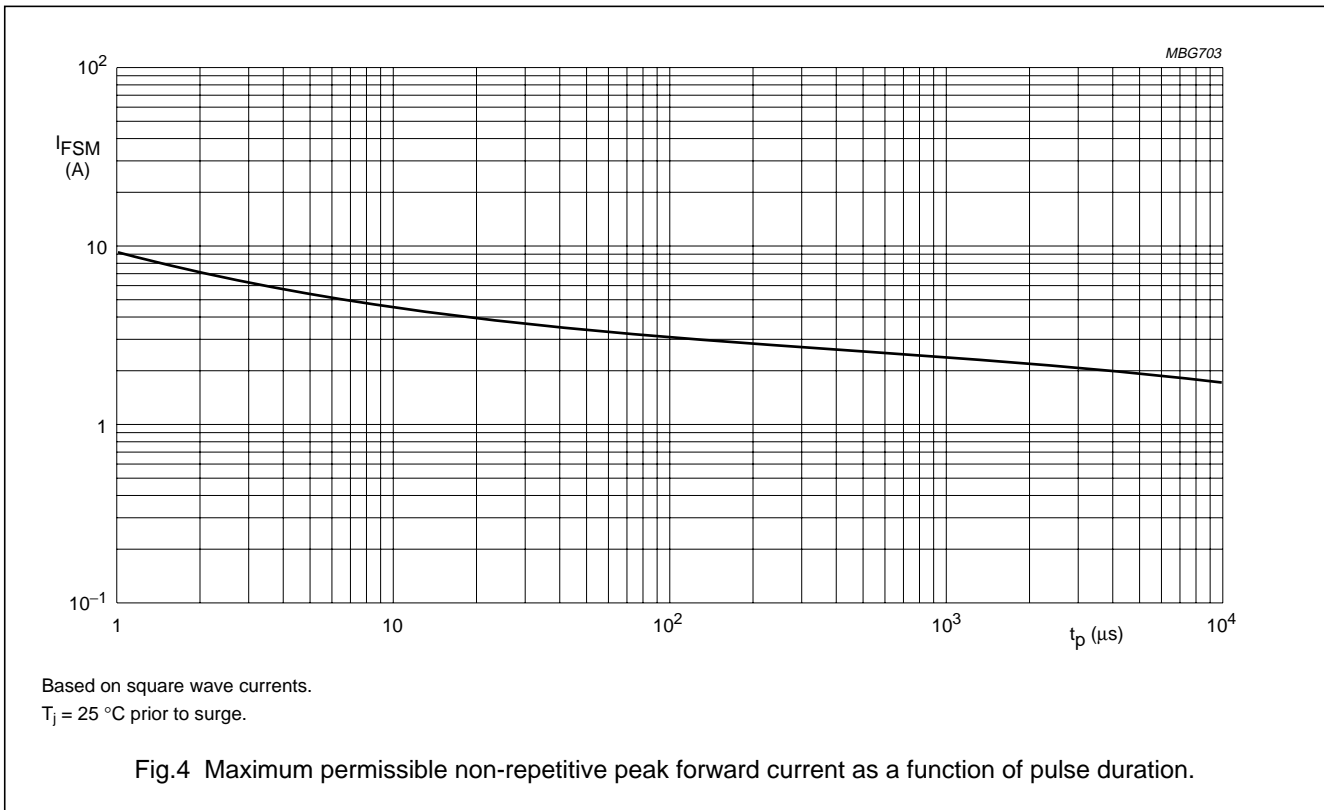
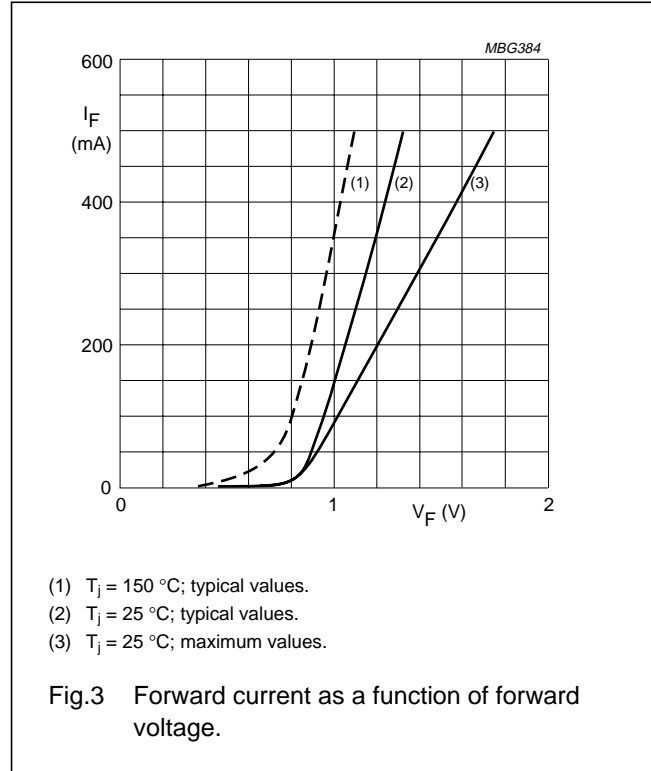
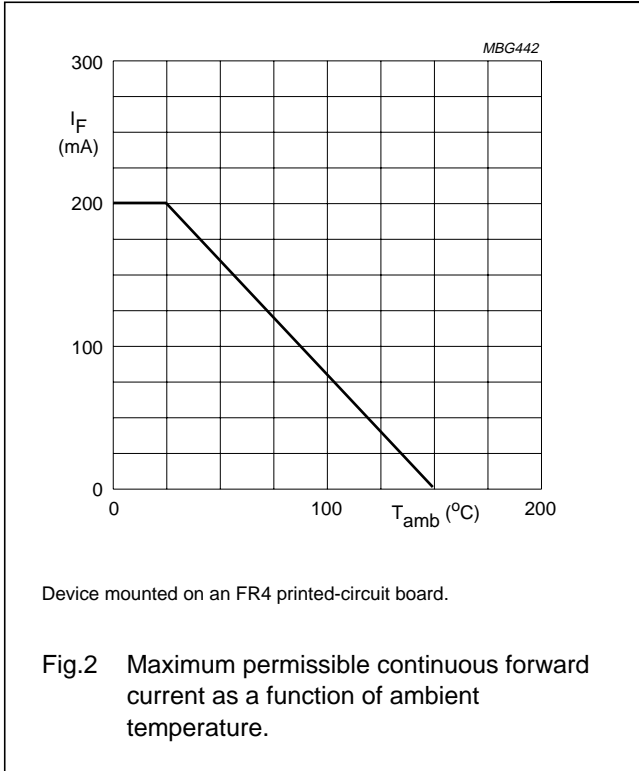
Note

1. Device mounted on an FR4 printed-circuit board.

General purpose diodes

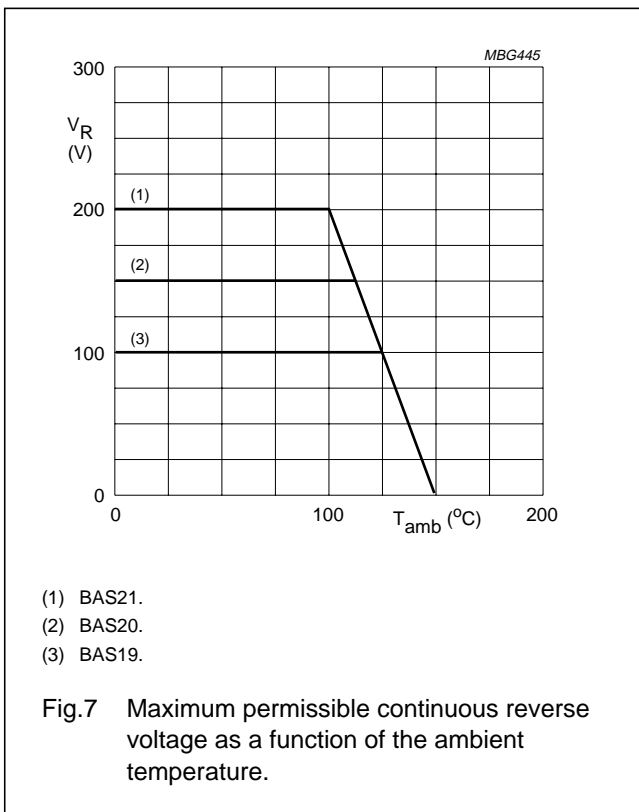
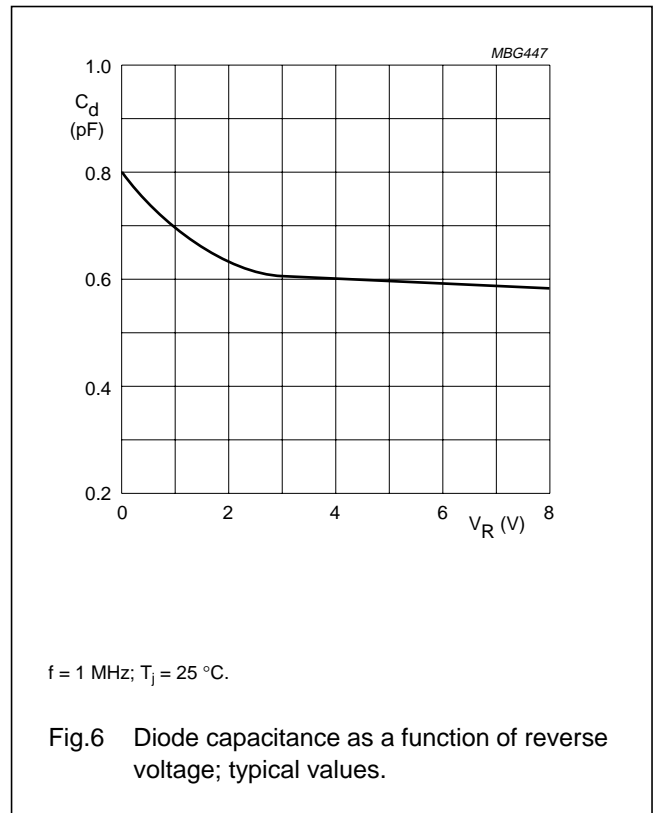
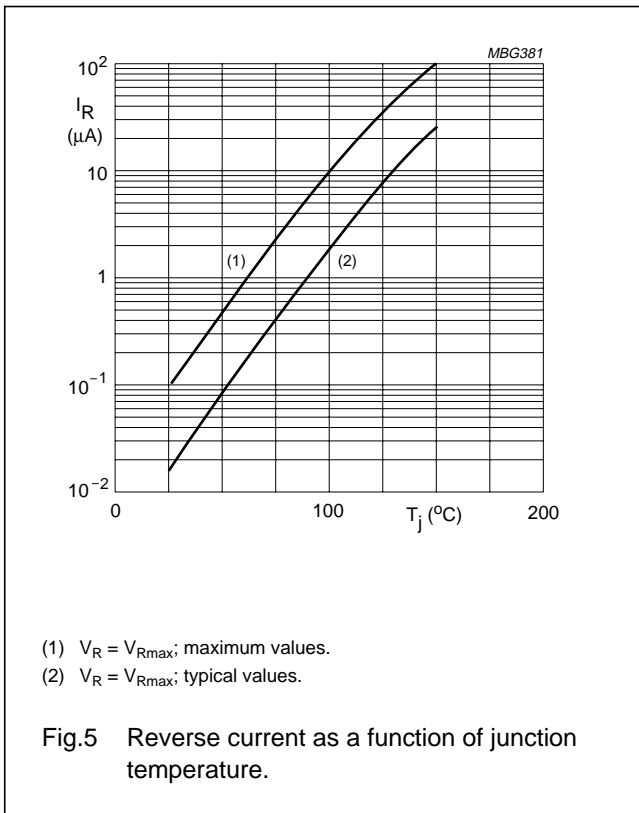
BAS19; BAS20; BAS21

GRAPHICAL DATA



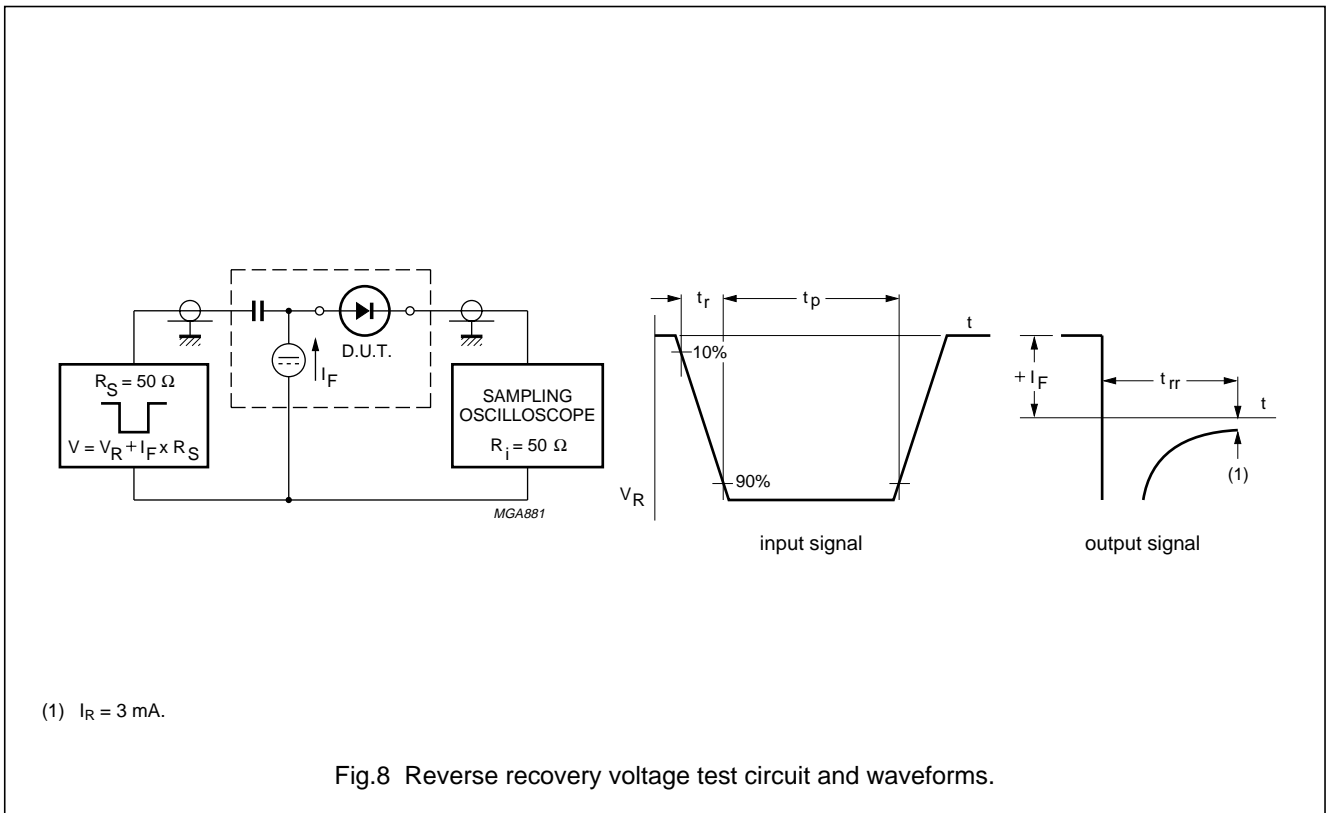
General purpose diodes

BAS19; BAS20; BAS21



General purpose diodes

BAS19; BAS20; BAS21



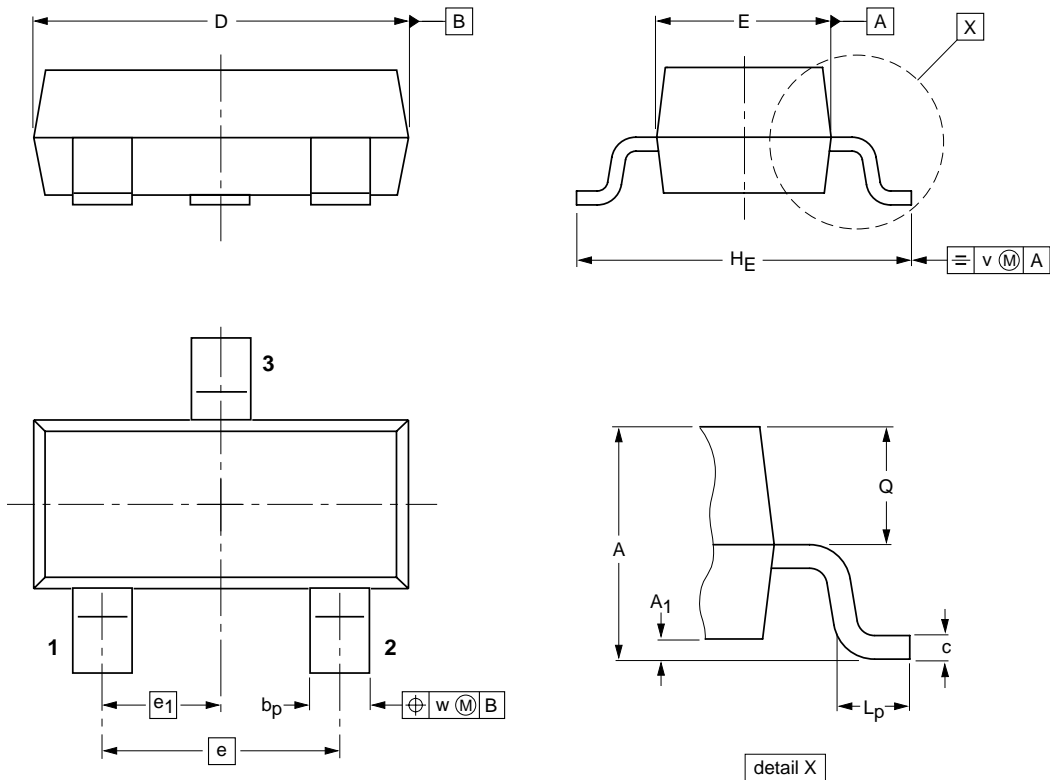
General purpose diodes

BAS19; BAS20; BAS21

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28- 99-09-13

Silicon Switching Diode

- For high-speed switching applications
- High breakdown voltage
- Pb-free (RoHS compliant) package ¹⁾
- Qualified according AEC Q101


BAS21

BAS21-03W

BAS21U


Type	Package	Configuration	Marking
BAS21	SOT23	single	JSs
BAS21-03W	SOD323	single	D
BAS21U	SC74	parallel triple	JSs

Maximum Ratings at $T_A = 25^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	200	V
Peak reverse voltage	V_{RM}	250	
Forward current	I_F	250	mA
Peak forward current	I_{FM}	625	
Peak forward current	I_{FM}	625	mA
Surge forward current, $t = 10 \mu\text{s}$	I_{FS}	4	A
Non-repetitive peak surge forward current	I_{FSM}	-	
Total power dissipation	P_{tot}		mW
BAS21, $T_S \leq 70^\circ\text{C}$		350	
BAS21-03W, $T_S \leq 124^\circ\text{C}$		250	
BAS21U, $T_S \leq 122^\circ\text{C}$		250	
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-65 ... 150	

¹Pb-containing package may be available upon special request

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point ¹⁾	R_{thJS}		K/W
BAS21		≤ 230	
BAS21-03W		≤ 105	
BAS21U		≤ 110	

Electrical Characteristics at $T_A = 25^\circ\text{C}$, unless otherwise specified

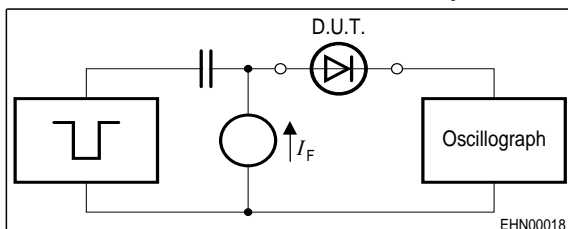
Parameter	Symbol	Values			Unit
		min.	typ.	max.	

DC Characteristics

Breakdown voltage $I_{(BR)} = 100 \mu\text{A}$	$V_{(BR)}$	250	-	-	V
Reverse current $V_R = 200 \text{ V}$ $V_R = 200 \text{ V}, T_A = 150^\circ\text{C}$	I_R	-	-	0.1 100	μA
Forward voltage $I_F = 100 \text{ mA}$ $I_F = 200 \text{ mA}$	V_F	-	-	1 1.25	V

AC Characteristics

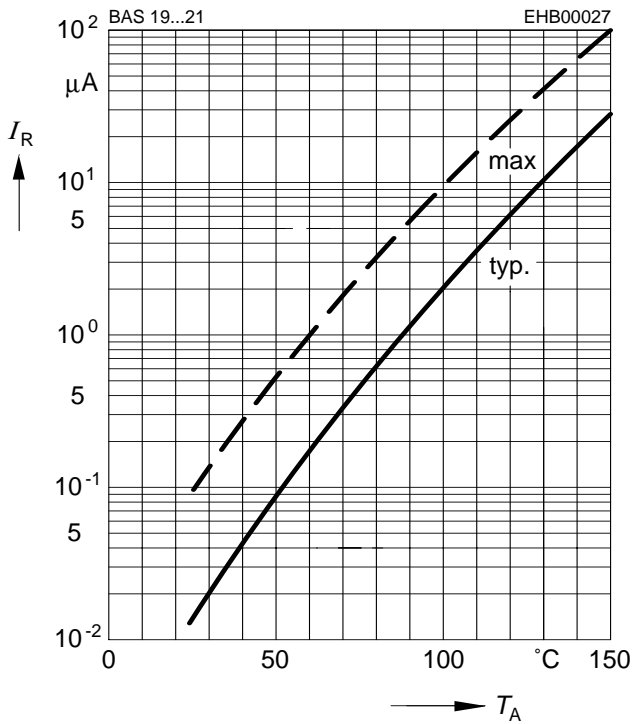
Diode capacitance $V_R = 0 \text{ V}, f = 1 \text{ MHz}$	C_T	-	-	5	pF
Reverse recovery time $I_F = 30 \text{ mA}, I_R = 30 \text{ mA}$, measured at $I_R = 3 \text{ mA}$, $R_L = 100 \Omega$	t_{rr}	-	-	50	ns

Test circuit for reverse recovery time

 Puls generator: $t_p = 1 \mu\text{s}$, $D = 0.05$
 $t_r = 0.6 \text{ ns}$, $R_i = 50 \Omega$

 Oscilloscope: $R = 50 \Omega$, $t_r = 0.35 \text{ ns}$, $C \leq 1 \text{ pF}$
¹⁾For calculation of R_{thJA} please refer to Application Note Thermal Resistance

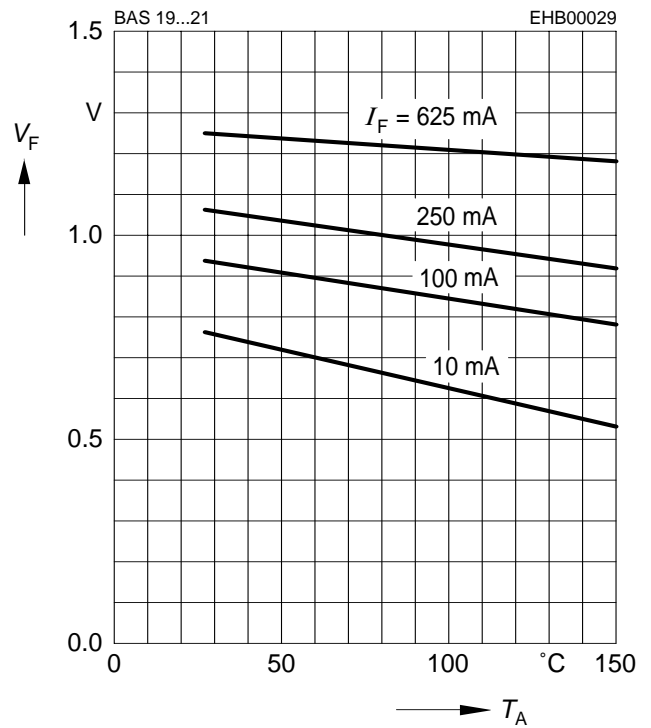
Reverse current $I_R = f(T_A)$

$V_R = 200V$

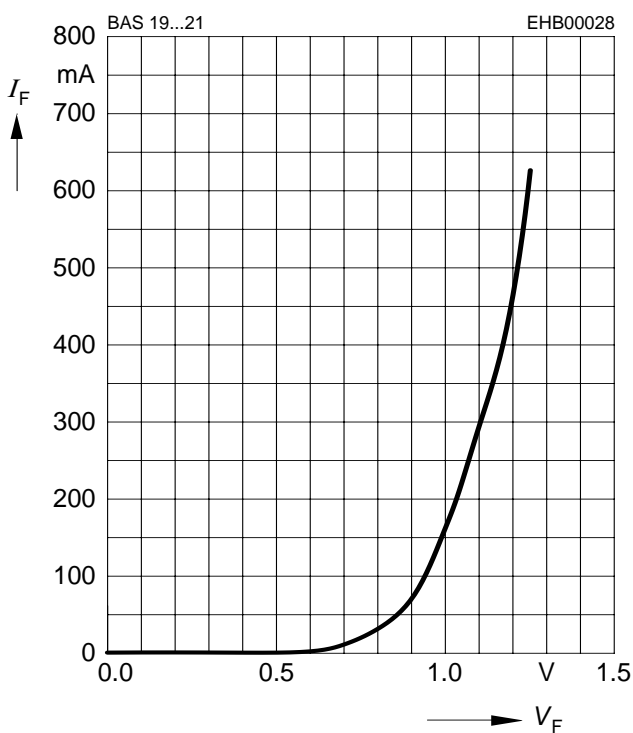


Forward Voltage $V_F = f(T_A)$

$I_F = \text{Parameter}$

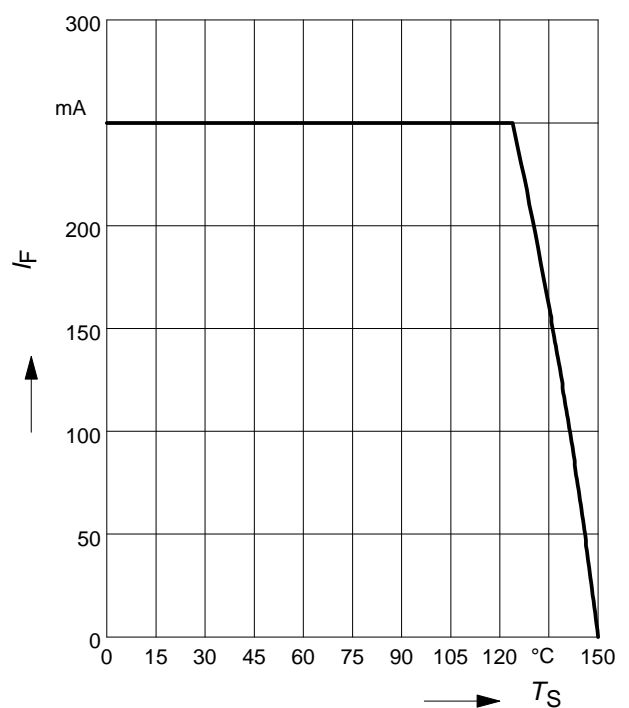


Forward current $I_F = f(V_F)$



Forward current $I_F = f(T_S)$

BAS21-03W



Forward current $I_F = f(T_S)$

BAS21U



Permissible Puls Load $R_{thJS} = f(t_p)$

BAS21



Permissible Pulse Load

$I_{Fmax} / I_{FDC} = f(t_p)$

BAS21



Permissible Puls Load $R_{thJS} = f(t_p)$

BAS21-03W



Permissible Pulse Load

$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAS21-03W



Permissible Puls Load $R_{thJS} = f(t_p)$

BAS21U



Permissible Pulse Load

$$I_{Fmax} / I_{FDC} = f(t_p)$$

BAS21U



Package Outline



Foot Print



Marking Layout (Example)

Small variations in positioning of Date code, Type code and Manufacture are possible.



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
 Reel ø330 mm = 10.000 Pieces/Reel

For symmetric types no defined Pin 1 orientation in reel.



Package Outline



Foot Print



Marking Layout (Example)



Standard Packing

Reel $\varnothing 180$ mm = 3.000 Pieces/Reel
 Reel $\varnothing 330$ mm = 10.000 Pieces/Reel

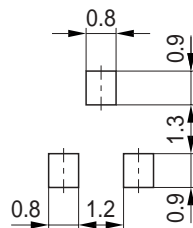


Package Outline



1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



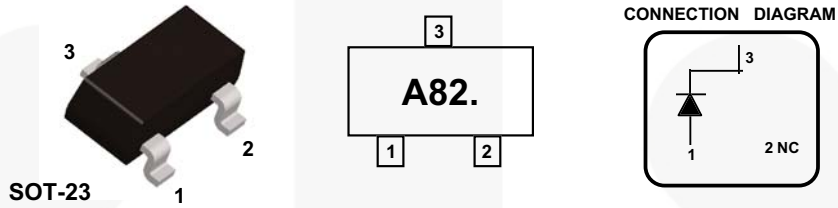
Standard Packing

Reel \varnothing 180 mm = 3.000 Pieces/Reel
 Reel \varnothing 330 mm = 10.000 Pieces/Reel





BAS21 General-Purpose High Voltage Diode



Ordering Information

Part Number	Top Mark	Package	Packing Method
BAS21	A82.	SOT-23 3L	Tape and Reel

Absolute Maximum Ratings^{(1), (2)}

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Value	Unit
W_{IV}	Working Inverse Voltage	250	V
I_O	Average Rectified Current	200	mA
I_F	DC Forward Current	600	mA
i_f	Recurrent Peak Forward Current	700	mA
$i_{f(\text{surge})}$	Peak Forward Surge Current	Pulse Width = 1.0 second	1.0
		Pulse Width = 1.0 microsecond	2.0
T_{STG}	Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_J	Operating Junction Temperature	150	$^\circ\text{C}$

Notes:

1. These ratings are based on a maximum junction temperature of 150°C .
2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P_D	Total Device Dissipation	350	mW
	Derate Above 25°C	2.8	mW/ $^\circ\text{C}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	357	$^\circ\text{C}/\text{W}$

Electrical Characteristics

Values are at $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
B_V	Breakdown Voltage	$I_R = 100 \mu\text{A}$	250		V
I_R	Reverse Voltage Leakage Current	$V_R = 200 \text{ V}$		100	nA
		$V_R = 200 \text{ V}, T_A = 150^\circ\text{C}$		100	μA
V_F	Forward Voltage	$I_F = 100 \text{ mA}$		1.0	V
		$I_F = 200 \text{ mA}$		1.25	V
C_O	Diode Capacitance	$V_R = 0, f = 1.0 \text{ MHz}$		5.0	pF
T_{RR}	Reverse Recovery Time	$I_F = I_R = 30 \text{ mA}, I_{RR} = 3.0 \text{ mA}, R_L = 100 \Omega$		50	nS

Typical Performance Characteristics

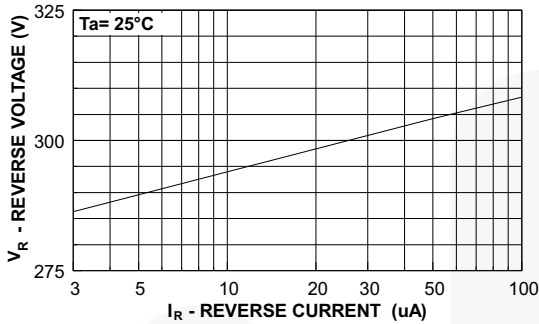


Figure 1. Reverse Voltage vs. Reverse Current
BV - 1.0 to 100 μ A

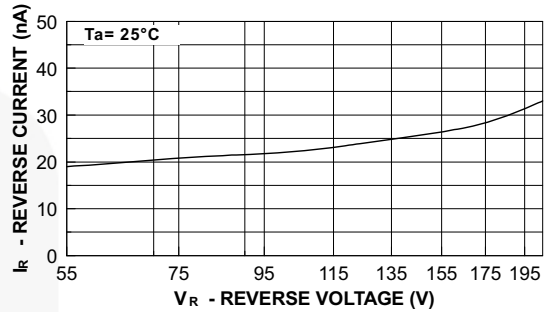


Figure 2. Reverse Current vs. Reverse Voltage
 I_R - 55 to 205 V

GENERAL RULE: The Reverse Current of a diode will approximately double for every ten (10) Degree C increase in Temperature

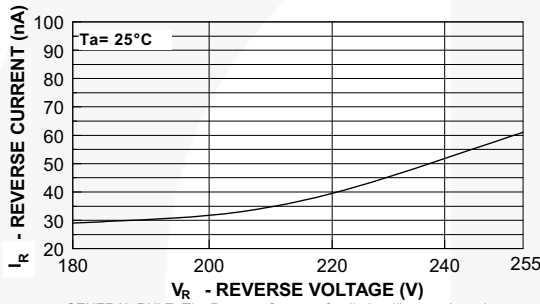


Figure 3. Reverse Current vs. Reverse Voltage
 I_R - 180 to 255 V

GENERAL RULE: The Reverse Current of a diode will approximately double for every ten Degree C increase in Temperature

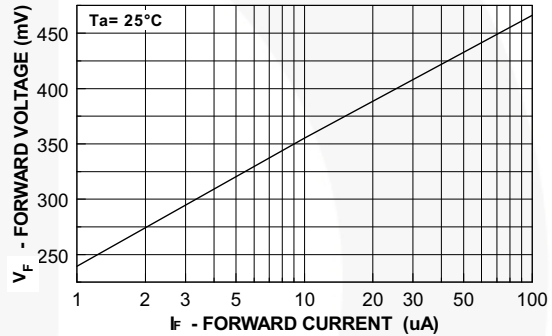


Figure 4. Forward Voltage vs. Forward Current
 V_F - 1.0 to 100 μ A

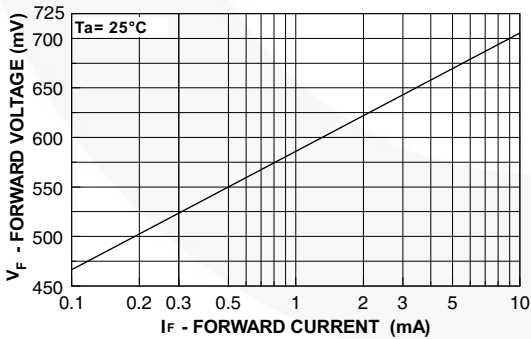


Figure 5. Forward Voltage vs. Forward Current
 V_F - 0.1 to 10 mA

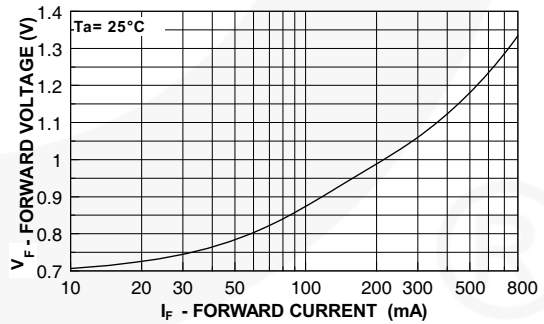


Figure 6. Forward Voltage vs. Forward Current
 V_F - 10 to 800 mA

Typical Performance Characteristics (Continued)

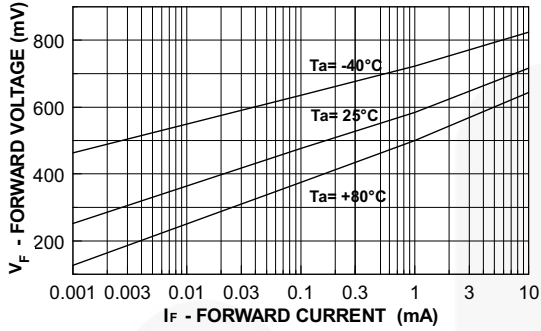


Figure 7. Forward Voltage vs. Ambient Temperature
 $V_F - 1.0 \mu A - 10 mA (-40 \text{ to } +80^\circ C)$

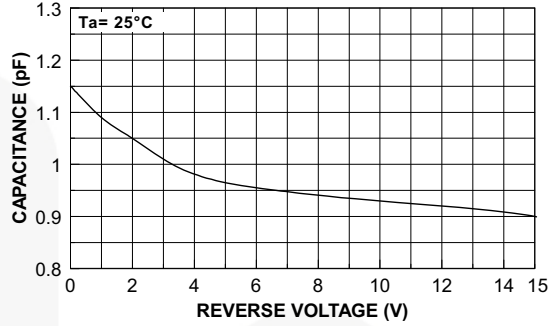


Figure 8. Capacitance vs. Reverse Voltage

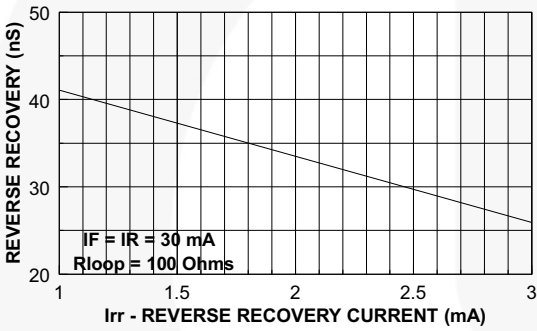


Figure 9. Reverse Recovery Time vs. Reverse Recovery Current (I_{rr})

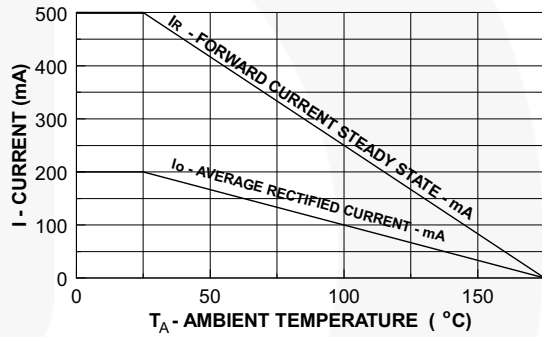


Figure 10. Average Rectified Current (I_O) and Forward Current (I_F) vs. Ambient Temperature (T_A)

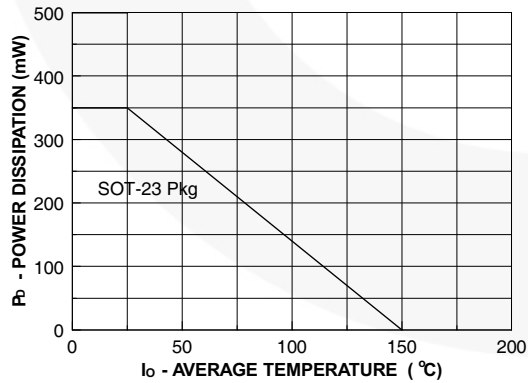


Figure 11. Power Derating Curve



LAND PATTERN
RECOMMENDATION



SEE DETAIL A



DETAIL A
SCALE: 2X

NOTES: UNLESS OTHERWISE SPECIFIED

- A) REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE H.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS ARE INCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS.
- D) DIMENSIONING AND TOLERANCING PER ASME Y14.5M - 2009.
- E) DRAWING FILE NAME: MA03DREV12

